210	210 210	210	210	210	210	
Regi	stration No :					
Total Nu	mber of Pages : 02				.Tech	
210	7 <sup>th</sup> Semester Re	gular Examinatio	on 2019-20	210 <b>PEI7</b>	7J005	
		MEMS				
		H : AEIE, EIE, IEI x Marks : 100	E			
		me : 3 Hours				
Answe	Q.C r Question No.1 (Part-1) which is	CODE : HR117 compulsorv. anv	/ EIGHT from F	Part-II and anv T	wo	
210	210 210 <b>f</b> ı	rom Part-III.	210	210	21	
	The figures in the rig	ht hand margin i	ndicate marks	•		
		Part- I				
<b>Q</b> 1	Only Short Answer Type Questions	s (Answer All-10)		(2	2 x 10)	
a)	What do you mean by SOC?					
<b>b)</b>	Illustrate the electrostatic actuation m	010	010	210	21	
210 <b>c)</b>	Define micromachining. Enlist differen		components.	210		
d)	Write the difference between wet and	•				
e)	What types of magnetic materials are					
f)	State the principle of pressure sensor					
g)	Write the principle of operation of ME		•			
h) 1)0	What do you understand from lift-off t Enlist various application areas of ME	•	210	210	210	
j)	Differentiate between pull-in voltage		for MEMS switch	nes.		
		Part- II				
Q2	Only Focused-Short Answer Type		ver Any Eight oເ	ut of Twelve) (	6 x 8)	
a)	Illustrate the important advantages	•	, ,	, ,	,	
210	systems? 210 210	210	210	210	210	
b)	Enlist various micro-sensing mechan					
c)	What do you understand from Ion steps.	Implantation Proces	ss? Briefly expla	ain its various		
d)	Compare surface and bulk micromac	hining techniques ir	n MEMS.			
<b>e</b> )	What are macro and micro fluids? Given	• •				
<b>f)</b>	Illustrate the wet etching process using	010	040	210	210	
g)	Discuss the steps involved in LTCC process by using suitable illustrations.					
h)	Explain different wafer bonding techn	•				
i)	Discuss in detail about the failure m MEMS devices.	echanisms and pov	wer handling cha	aracteristics of		
j)	What is CVD? Explain the different pa					
	Fabricate a Cantilever beam using E					
<b>k)</b> 210	technique and compare between these	se two techniques. I	Use suitable illus	trations <sub>:0</sub>	210	

210		210		210	210	210	210	210	210	
210	Q3	210	Write the p	•	Part Questions (Answation of MEMS renes.	er Any Two out	•	of MEMS	<b>(16)</b> <sup>210</sup>	
	Q4	a)	Enlist some limitations of photolithography. Compare between optical lithography and soft lithography.							
210	Q5	<b>b)</b> 210	How does Discuss th	an MEMS gyros	poration and Spu scope work? Defi techniques used f DSA.	210 ne coriolis force	and coriolis acce		(8) (16)	
	Q6	a)	Write short answer on following : LIGA							
210		•	PDMS	210	210	210	210	210	210	
210		210		210	210	210	210	210	210	
210		210		210	210	210	210	210	210	
210		210		210	210	210	210	210	210	
210		210		210	210	210	210	210	210	